

2823

#8/IDS



35.C10530C/D2

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
KIYOFUMI SAKAGUCHI, ET AL.) : Examiner: E. Abbott
Application No.: 09/161,774) :
Filed: September 29, 1998) : Group Art Unit: 2823
For: PROCESS FOR PRODUCTION) :
OF SEMICONDUCTOR) :
SUBSTRATE) : January 12, 2000

RECEIVED

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TECHNOLOGY CENTER 2800

Assistant Commissioner for Patents
Washington, D.C. 20231

SECOND INFORMATION DISCLOSURE STATEMENT

Sir:

In compliance with the duty of disclosure under
37 C.F.R. § 1.56 and in accordance with the practice under
37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is
directed to the documents listed on the enclosed Form
PTO-1449.

Applicants note that inclusion of documents in this
statement does not constitute a representation that these
documents are prior art. Moreover, Applicants wish to point
out they have cited the references listed on the face of
Matsushita, U.S. 5,811,348. Applicants have copied claims

from the Matsushita patent. (See Second and Third Preliminary Amendments dated September 22, 1999.)

The Examiner's attention is also directed to the following U.S. Applications:

<u>APPLICATION NO.</u>	<u>FILING DATE</u>	<u>GROUP ART UNIT</u>
09/161,775	09/29/98	2813
08/818,239	03/14/97	Unknown

Applicants believe EPO 797 258 A2 corresponds to pending U.S. application 08/818,239 filed March 14, 1997. This application would be a continuation-in-part of Application No. 08/595,382, which has issued as Matsushita, U.S. 5,811,348. As noted above, Applicants have copied the claims of the '348 patent. U.S. Application 09/161,775 is related to the present application, as they are both divisionals of the same parent application.

In accordance with 37 C.F.R. § 1.98(a)(2)(iii), no copy of any cited U.S. Application is enclosed.

Additionally, to complete the record, Applicants wish to make the Examiner aware of the following documents which are related to the claimed technology, even though they plainly do not constitute prior art in the present case. These documents are also listed on the attached PTO-1449.

1. T. Yonehara et al., "Epitaxial layer transfer by bond and etch back of porous Si", Appl. Phys. Lett. 64(16), 2108-2110 (1994);
2. Nikkei Microdevice, pp. 76-77 (1994) (with translation);
3. Extended Abstracts (the 57th Autumn Meeting, 1996); The Japan Society of Applied Physics (Abstr. 8a-V-8) (with translation);
4. Extended Abstracts (The 44th Spring Meeting, 1997); The Japan Society of Applied Physics and Related Societies (Abstr. 31a-B-5) (with translation);
5. Extended Abstracts (The 59th Autumn Meeting, 1998); The Japan Society of Applied Physics (Abstr. 15a-YB-4) (with translation);
6. Y. Hashimoto, "Shin-Kagaku Yougo Jiten" (new chemical term dictionary), Sankyo Shuppan Co., Ltd., 6th Edn. (1973) (definition of anodic oxidation) (with translation);
and
7. H. Tayanaka, et al., "Thin-Film Crystalline Silicon Solar Cells Obtained by Separation of a Porous Silicon Sacrificial Layer" 2d World Conf. and Exhibition on Photovoltaic Solar Energy Conversion (1998).


Please note the translations for items 3-6 above are provided sequentially in the same document.

CONCLUSION

It is respectfully requested that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be returned indicating that such information has been considered.

Applicants' undersigned attorney may be reached in our New York office by telephone at (212) 218-2100. All correspondence should be directed to our address given below.

Respectfully submitted,


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